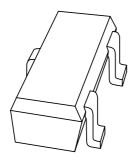
DISCRETE SEMICONDUCTORS

DATA SHEET



2PB709AWPNP general purpose transistor

Product specification

2002 Jun 26





PNP general purpose transistor

2PB709AW

FEATURES

- High collector current (max. 100 mA)
- Low collector-emitter saturation voltage (max. 500 mV).

APPLICATIONS

· General purpose switching and amplification.

DESCRIPTION

PNP transistor in an SC-70 (SOT323) plastic package. NPN complement: 2PD601AW

MARKING

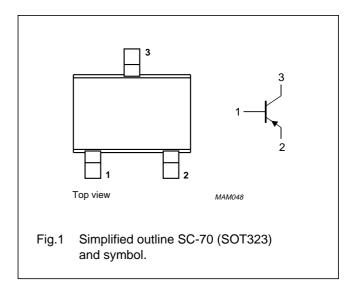
TYPE NUMBER	MARKING CODE(1)
2PB709AQW	N5*
2PB709ARW	N7*
2PB709ASW	N9*

Note

- 1. * = p: made in Hong Kong.
 - * = t: made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-45	V
V _{CEO}	collector-emitter voltage	open base	_	-45	V
V _{EBO}	emitter-base voltage	open collector	_	-6	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18".

PNP general purpose transistor

2PB709AW

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18".

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	PARAMETER CONDITIONS			
I _{CBO}	collector-base cut-off current	I _E = 0; V _{CB} = -45 V	_	-10	nA
		$I_E = 0$; $V_{CB} = -45 \text{ V}$; $T_j = 150 ^{\circ}\text{C}$	_	- 5	μΑ
I _{EBO}	emitter-base cut-off current	$I_C = 0; V_{EB} = -5 V$	_	-10	nA
h _{FE}	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -10 \text{ V}$			
	2PB709AQW		160	260	
	2PB709ARW		210	340	
	2PB709ASW		290	460	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -100 \text{ mA}; I_B = -10 \text{ mA};$ note 1	_	-500	mV
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = -10 V; f = 1 MHz	_	5	pF
f _T	transition frequency	$I_C = -1 \text{ mA}; V_{CE} = -10 \text{ V};$			
	2PB709AQW	f = 100 MHz	60	_	MHz
	2PB709ARW		70	_	MHz
	2PB709ASW		80	_	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

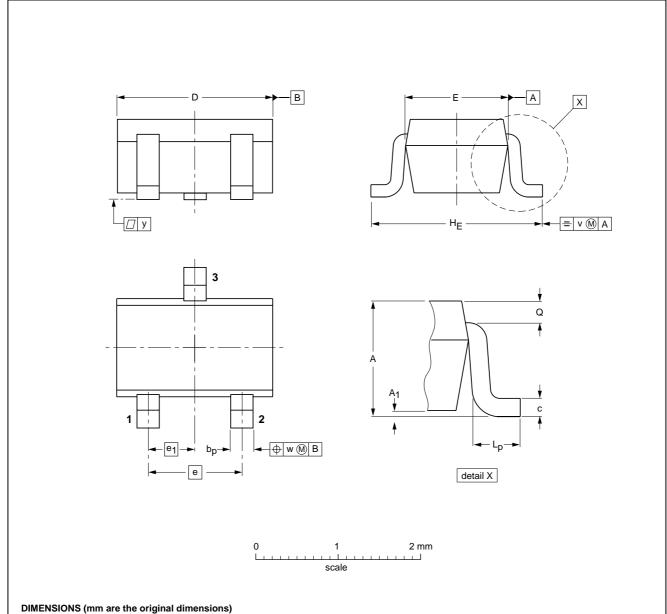
PNP general purpose transistor

2PB709AW

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENS	IONS (II	ım are t	ne origii	iai dime	insions)	
						7

UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	EUROPEAN ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT323			SC-70			97-02-28

PNP general purpose transistor

2PB709AW

DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes, without notice, in the products, including circuits, standard cells, and/or software, described or contained herein in order to improve design and/or performance. Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

PNP general purpose transistor

2PB709AW

NOTES

PNP general purpose transistor

2PB709AW

NOTES

Philips Semiconductors – a worldwide company

Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

© Koninklijke Philips Electronics N.V. 2002

SCA74

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

613514/01/pp8

Date of release: 2002 Jun 26

Document order number: 9397 750 09758

Let's make things better.

Philips Semiconductors



